

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
05 November 2020 (05.11.2020)



(10) International Publication Number
WO 2020/223029 A1

(51) International Patent Classification:

C09G 1/02 (2006.01) H01L 21/3105 (2006.01)
C09K 3/14 (2006.01) H01L 21/02 (2006.01)
B24B 37/04 (2006.01)

(21) International Application Number:

PCT/US2020/028463

(22) International Filing Date:

16 April 2020 (16.04.2020)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:

62/840,338 29 April 2019 (29.04.2019) US

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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ,
CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO,
DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN,
HR, HU, ID, IL, IN, IR, IS, JO, JP, KE, KG, KH, KN, KP,
KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME,
MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ,
OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA,
SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR,
TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ,
UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ,

(54) Title: SELECTIVE CHEMICAL MECHANICAL PLANARIZATION POLISHING

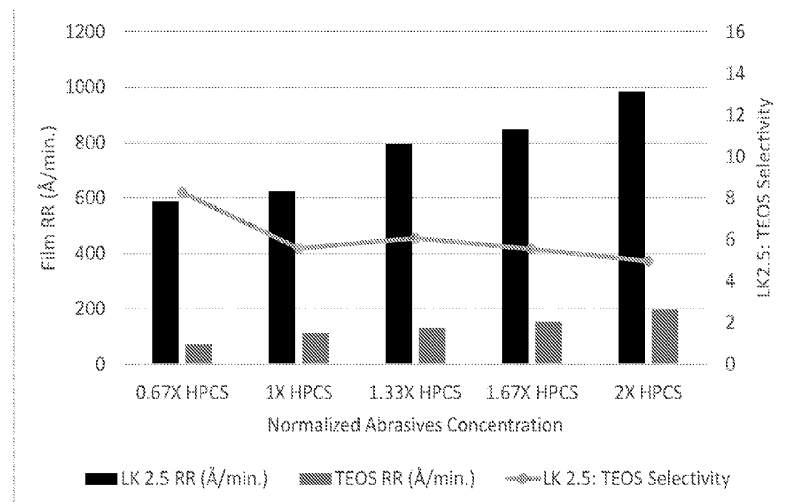


Figure. 1

(57) Abstract: Chemical Mechanical Planarization (CMP) polishing compositions, methods and systems are used to polish low-k or ultra-low-k films with reasonable high removal rates while to polish oxide and nitride films with relative low removal rates. The compositions use 5 abrasive, chemical additives to boost low-k or ultra-low-k film removal rates and suppress oxide and nitride film removal rates for achieving high selectivity, such as low-k: TEOS, ultra-low-k: TEOS, and low-k: SiN or ultra-low-k: SiN.

[Continued on next page]

WO 2020/223029 A1

TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*